

# *Resistive Switching Memory Model using NovaTCAD*

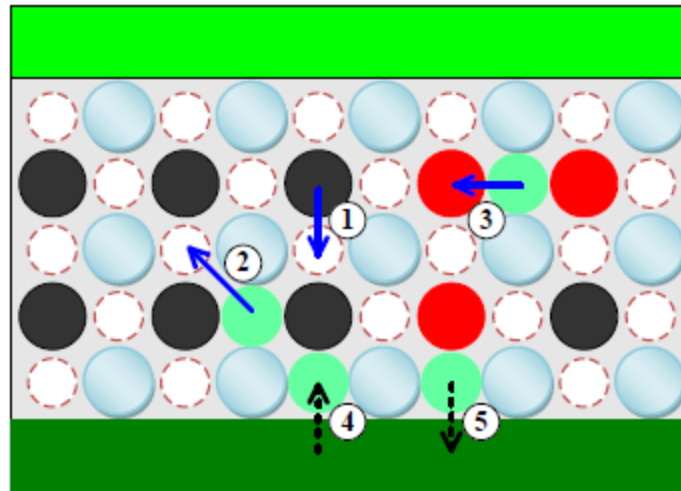
**-Based on Monte Carlo Simulation  
of O<sub>2</sub> diffusions**



# Resistive switching physical processes

- Temperature activated O<sub>2</sub> generation and recombination.
- Temperature activated hopping of O<sub>2</sub> at interstitial sites.
- Poole-Frenkel de-trapping model for off state leakage current.
- Absorption and release of O<sub>2</sub> by electrodes.
- Physical based probabilities with field and temperature dependence.
- O<sub>2</sub> site represented by a circuit node in Crosslight MiniSpice model.
- MiniSpice special resistor models: models based on  $\sinh()$  function and quantum point contact.
- MiniSpice included in NovaTCAD as Mixmode device simulation.

# Resistive switching Monte-Carlo approach



- $V_O$     ●  $O^{2-}$        Interstitial site
- Metal atom    ● Oxygen on lattice site
- ↓ ①  $V_O$  generation    ↙ ②  $O^{2-}$  hopping
- ← ③ Recombination between  $O^{2-}$  and  $V_O$
- ↑ ④  $O^{2-}$  release/absorb by electrode    ↓ ⑤  $O^{2-}$  release/absorb by electrode

$V_O$  generation rate, with  $E_a$  as activation energy,  $\Delta\phi$  as barrier lowered by field

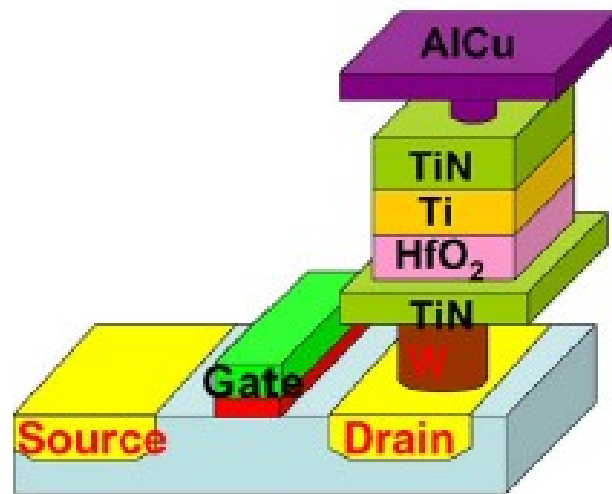
$$P_a = f \exp\left(-\frac{E_a - \Delta\phi_1}{k_B T_{loc}}\right)$$

Interstitial  $O_2$  hopping rate with  $E_h$  as activation energy.

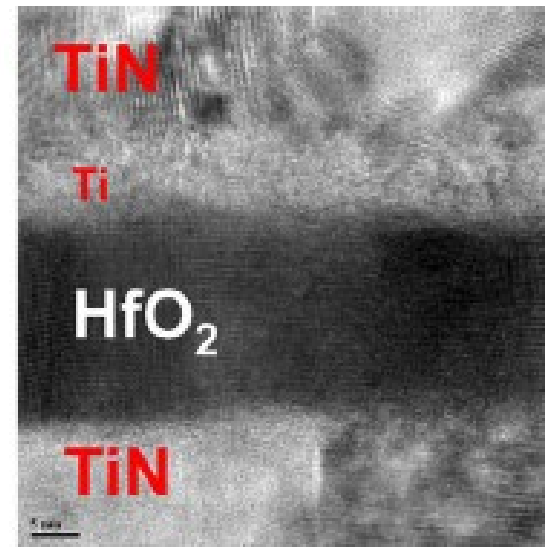
$$P_h = f \exp\left(-\frac{E_h - \Delta\phi_2}{k_B T_{loc}}\right)$$

[1] Peng Huang, Bin Gao, Bing Chen, Feifei Zhang, Lifeng Liu, Gang Du, Jinfeng Kang, Xiaoyan Liu, "Stochastic Simulation of Forming, SET and RESET Process for Transition Metal Oxide-based Resistive Switching Memory," SISPAD 2012, Sept. 5-7, 2012, Denver, CO, USA

# Demo Structure

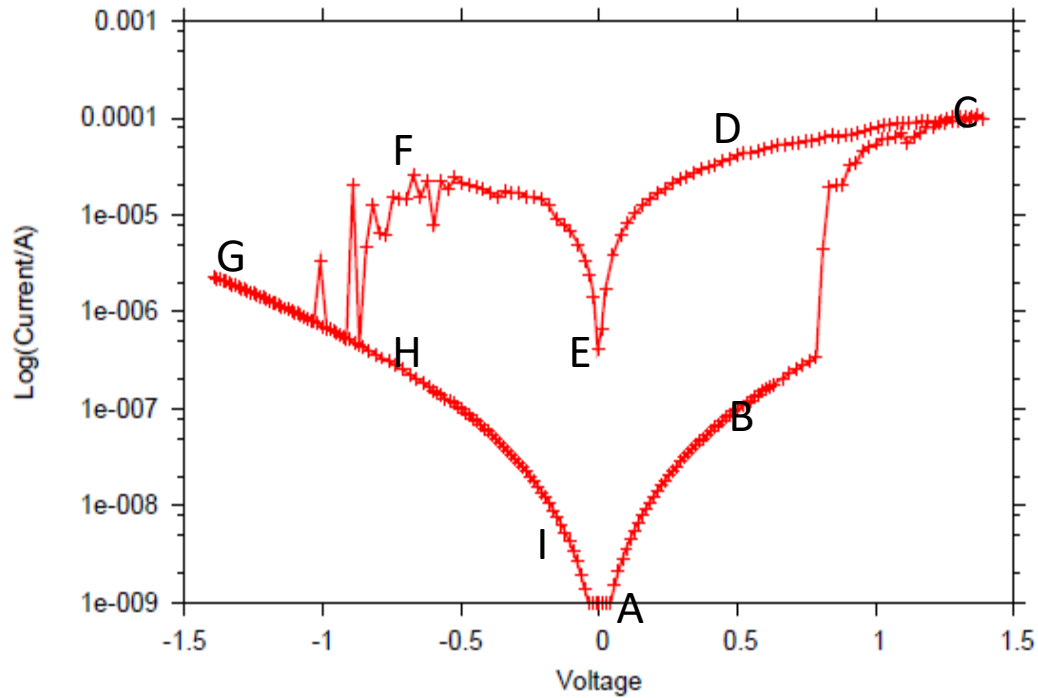


(a)



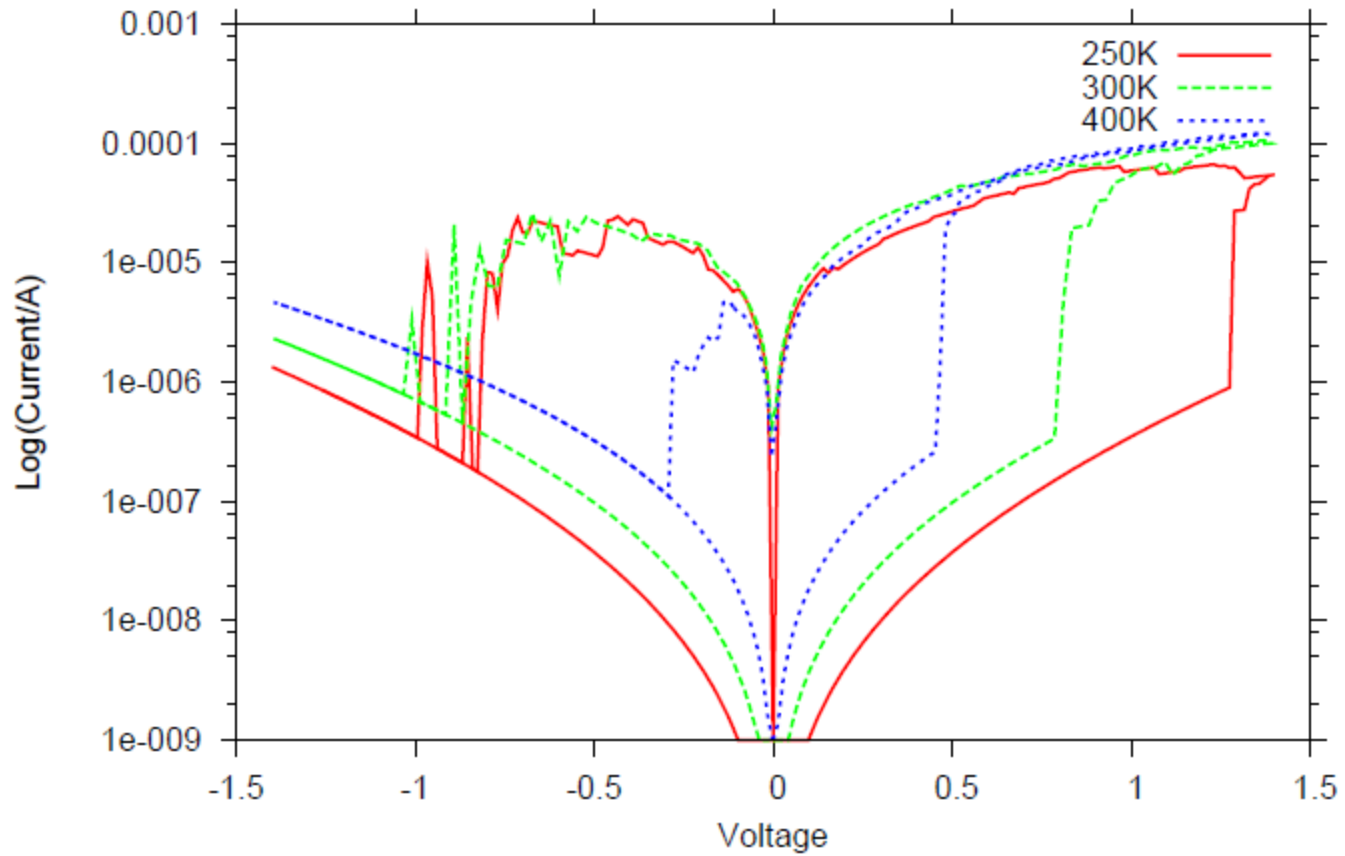
(b)

Resistive Switching Model Preview

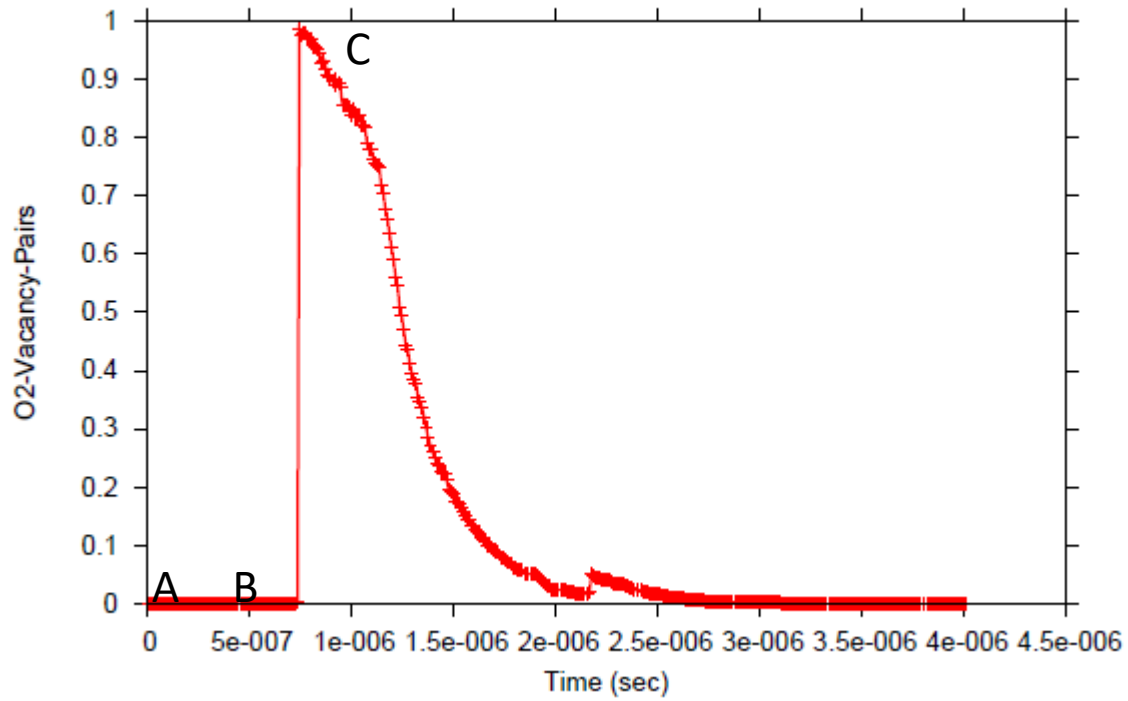


- A: Initial
- B: set\_half\_up
- C: set\_up
- D: set\_half\_down
- E: set\_down
- F: reset\_half\_up
- G: reset\_up
- H: reset\_half\_down
- I: reset\_down

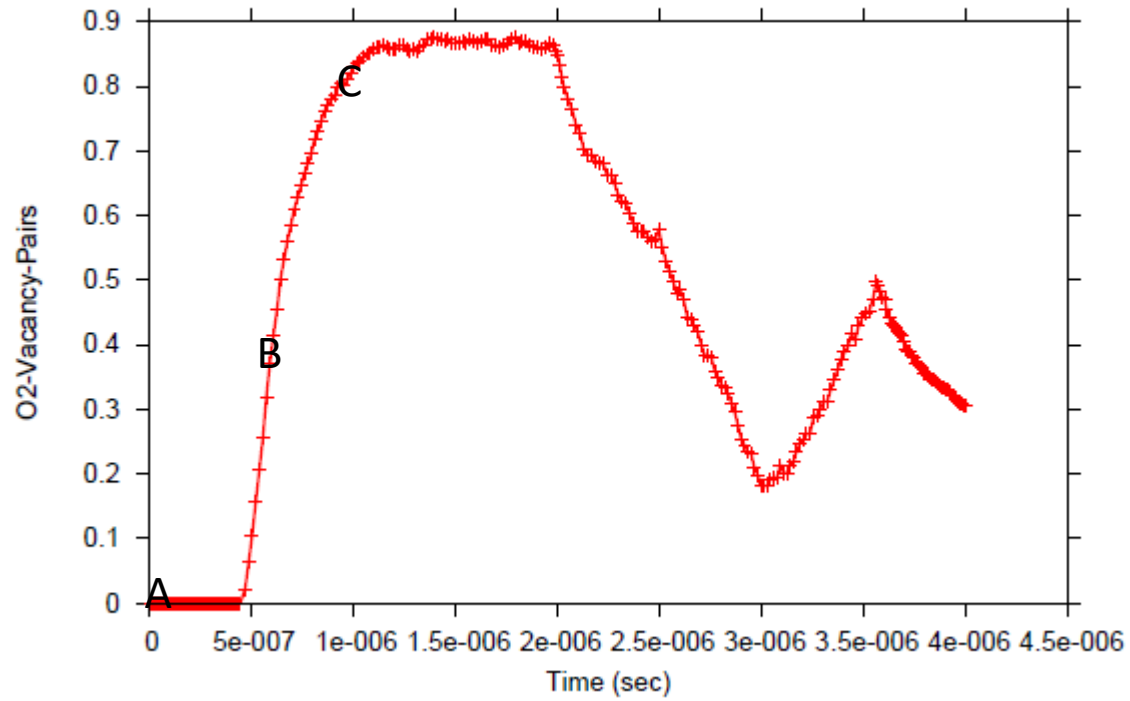
### Resistive Switching Model Preview



Resistive Switching Model Preview

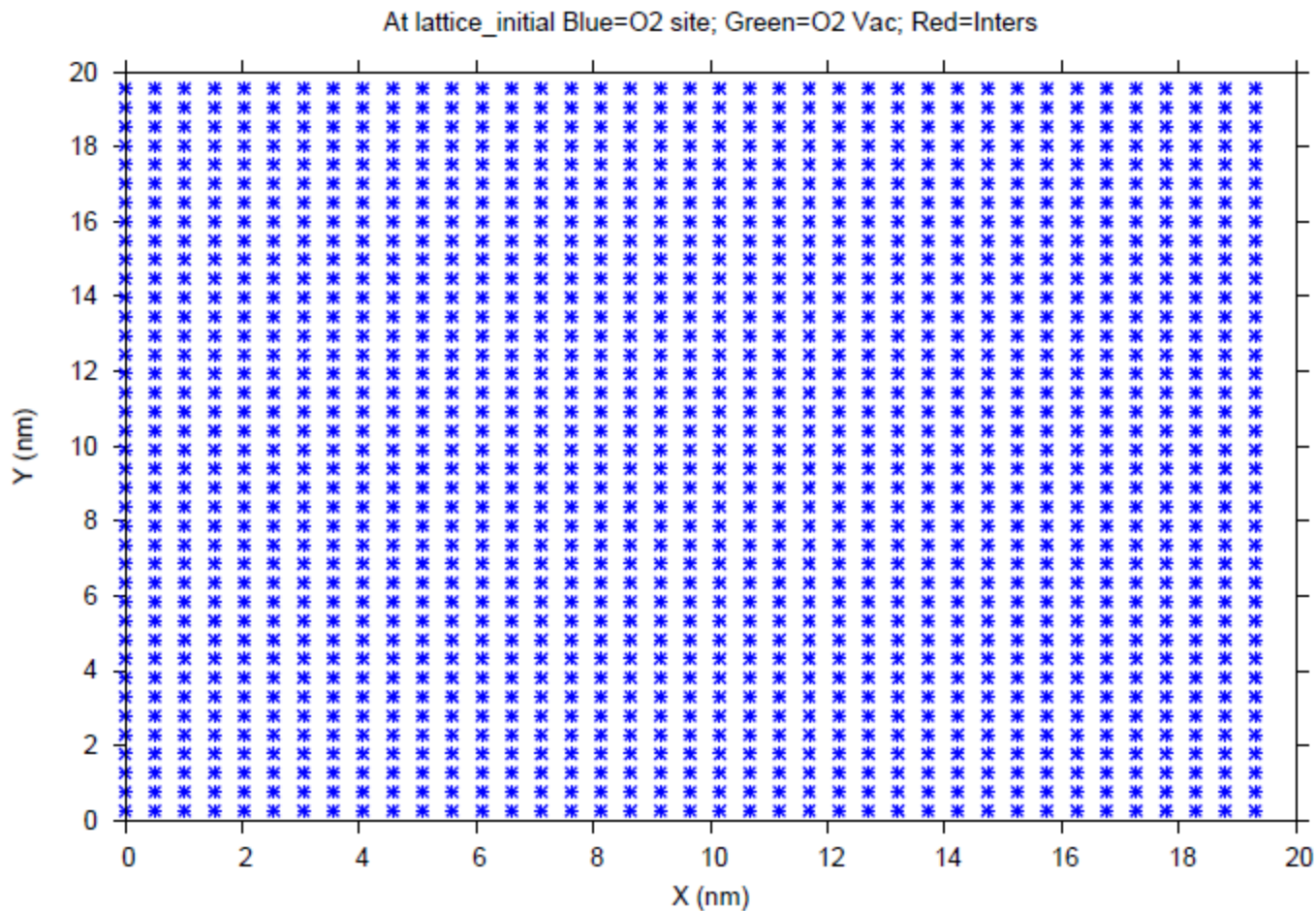


Resistive Switching Model Preview

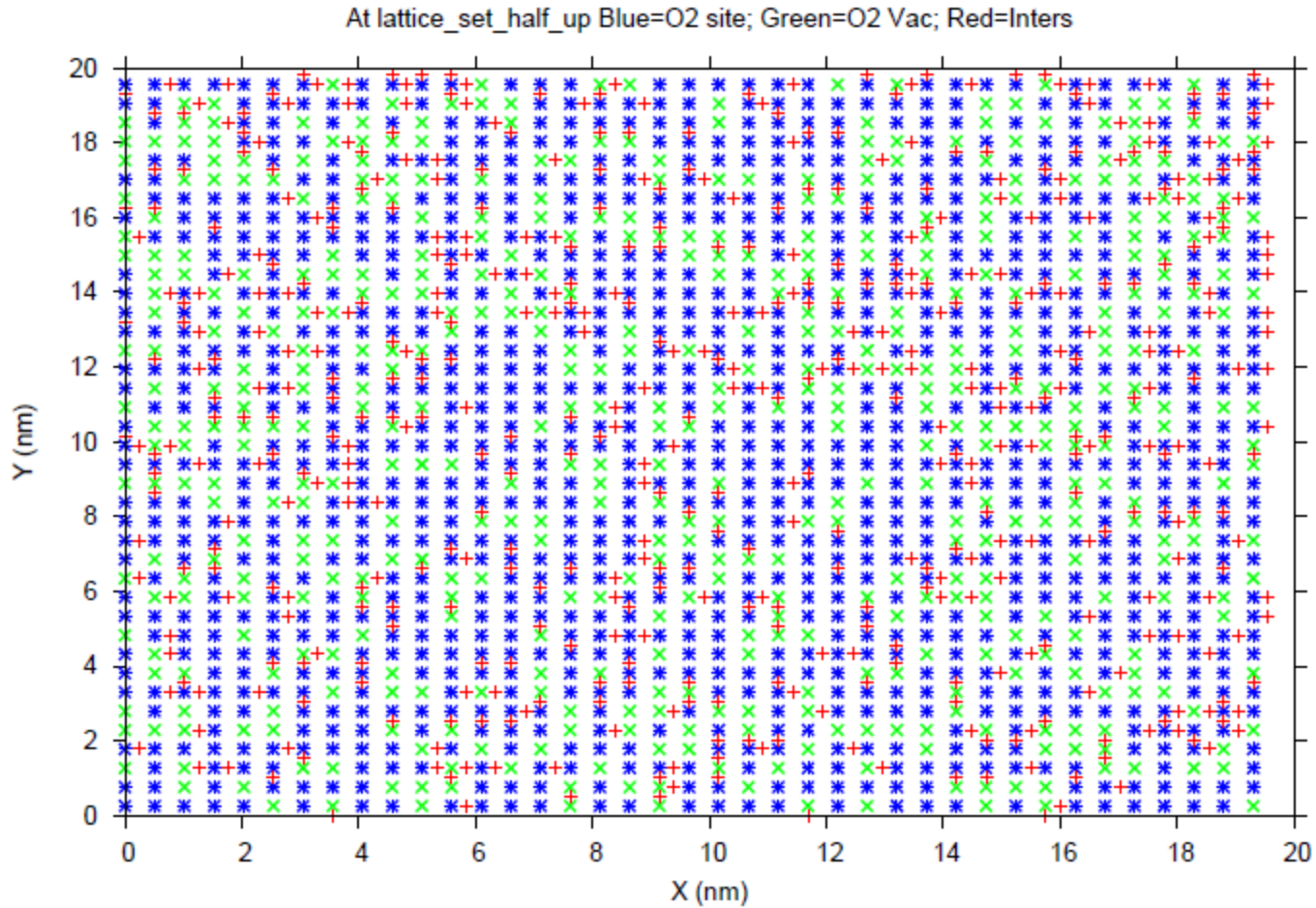




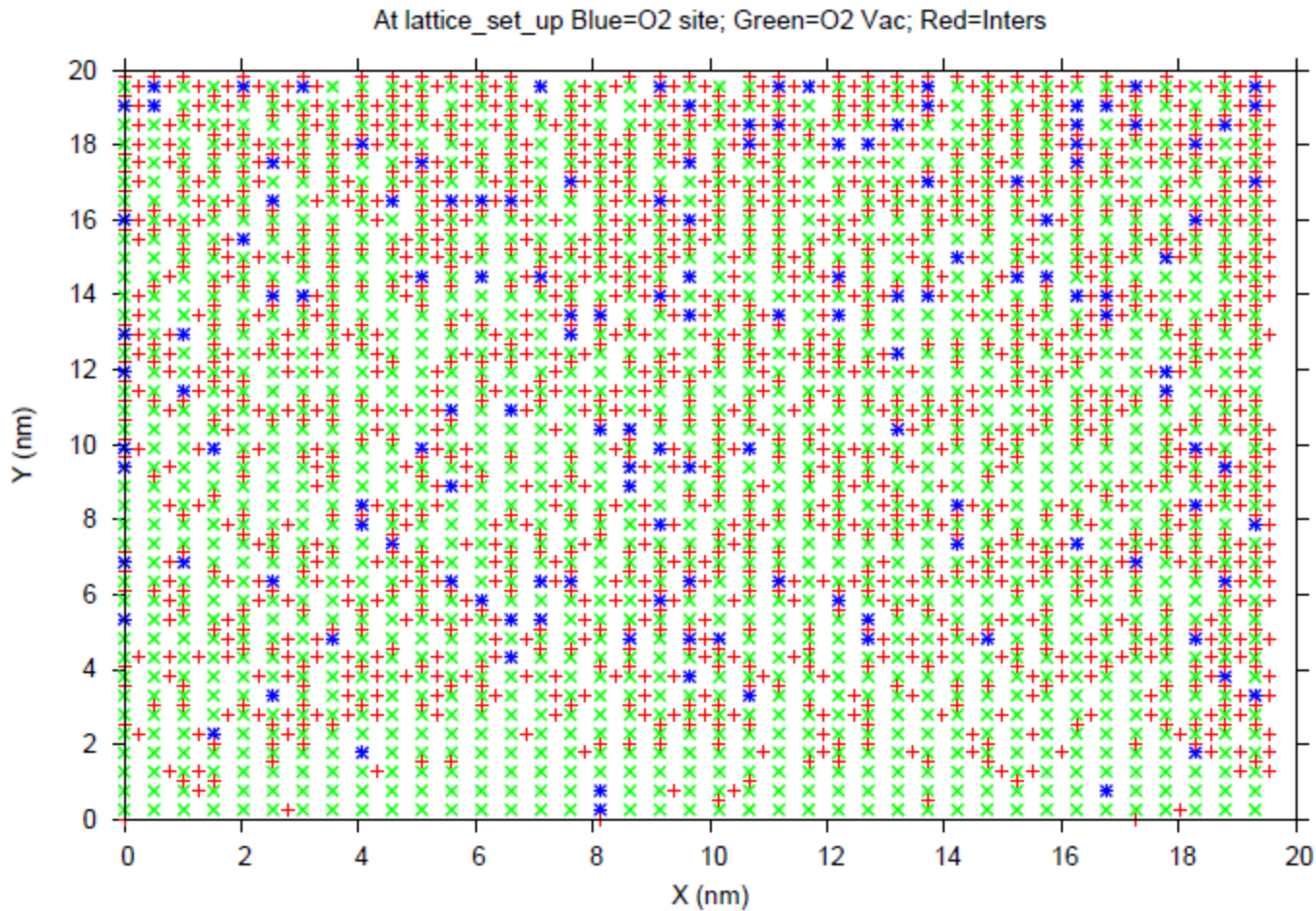
A



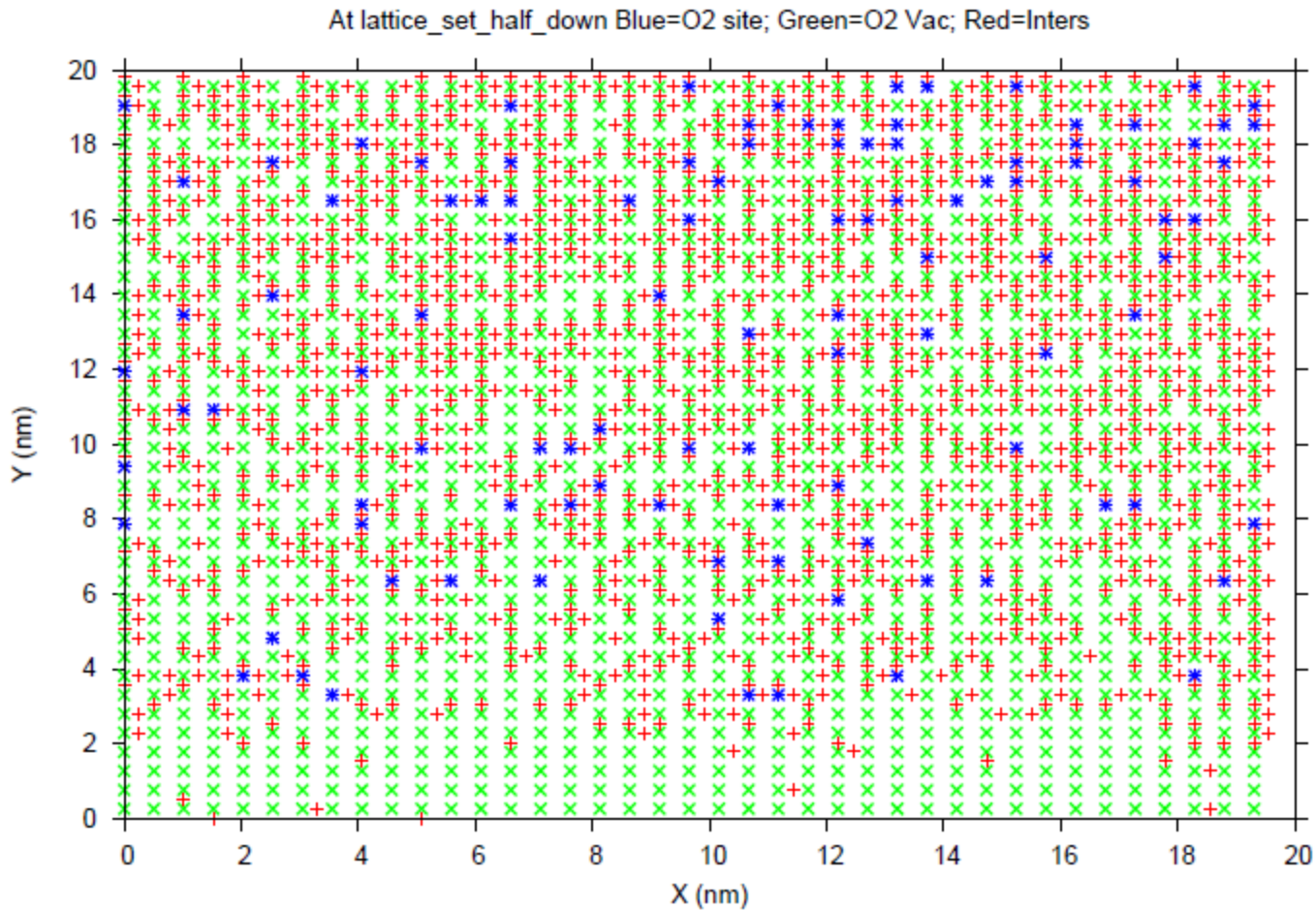
B:



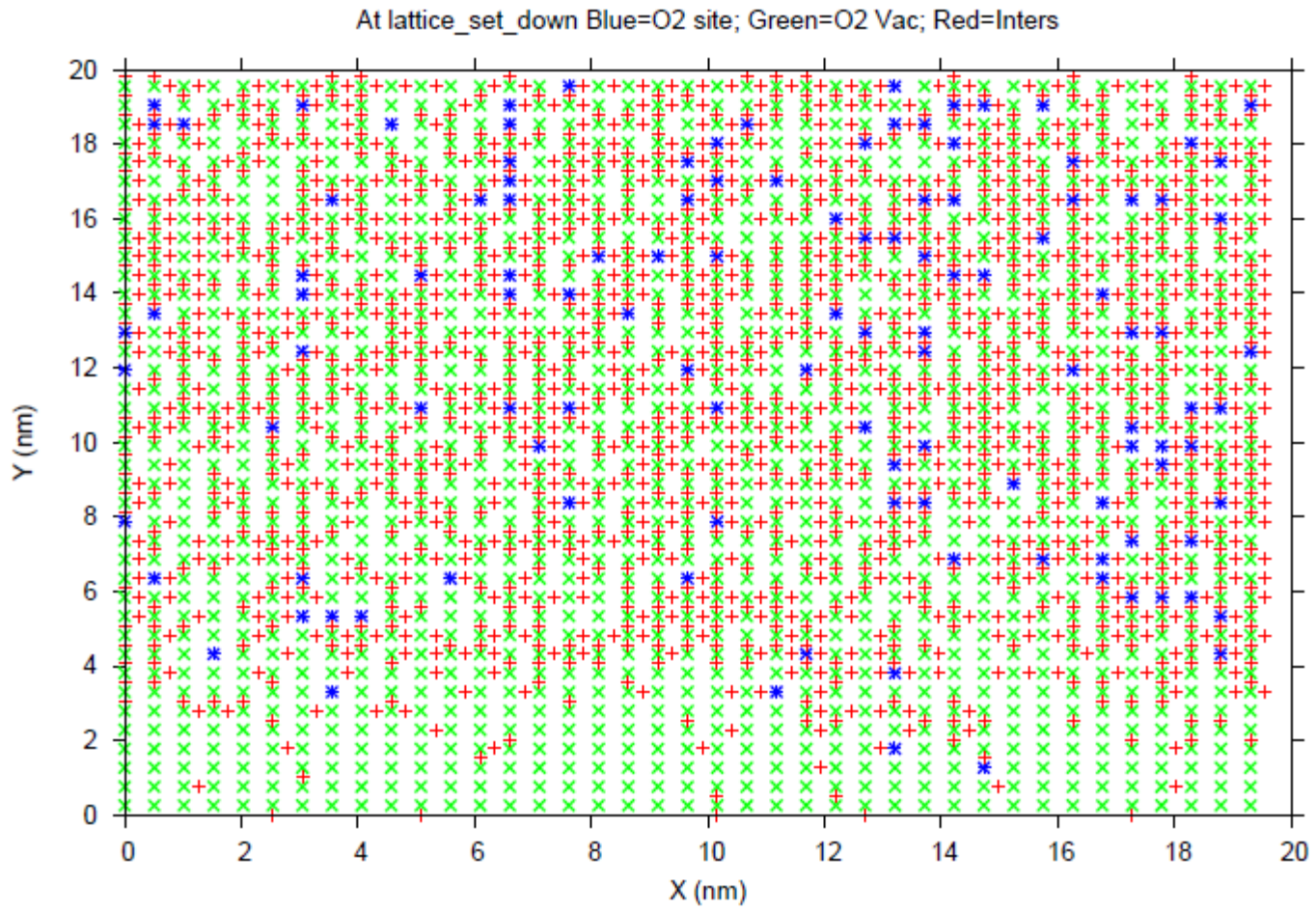
C:



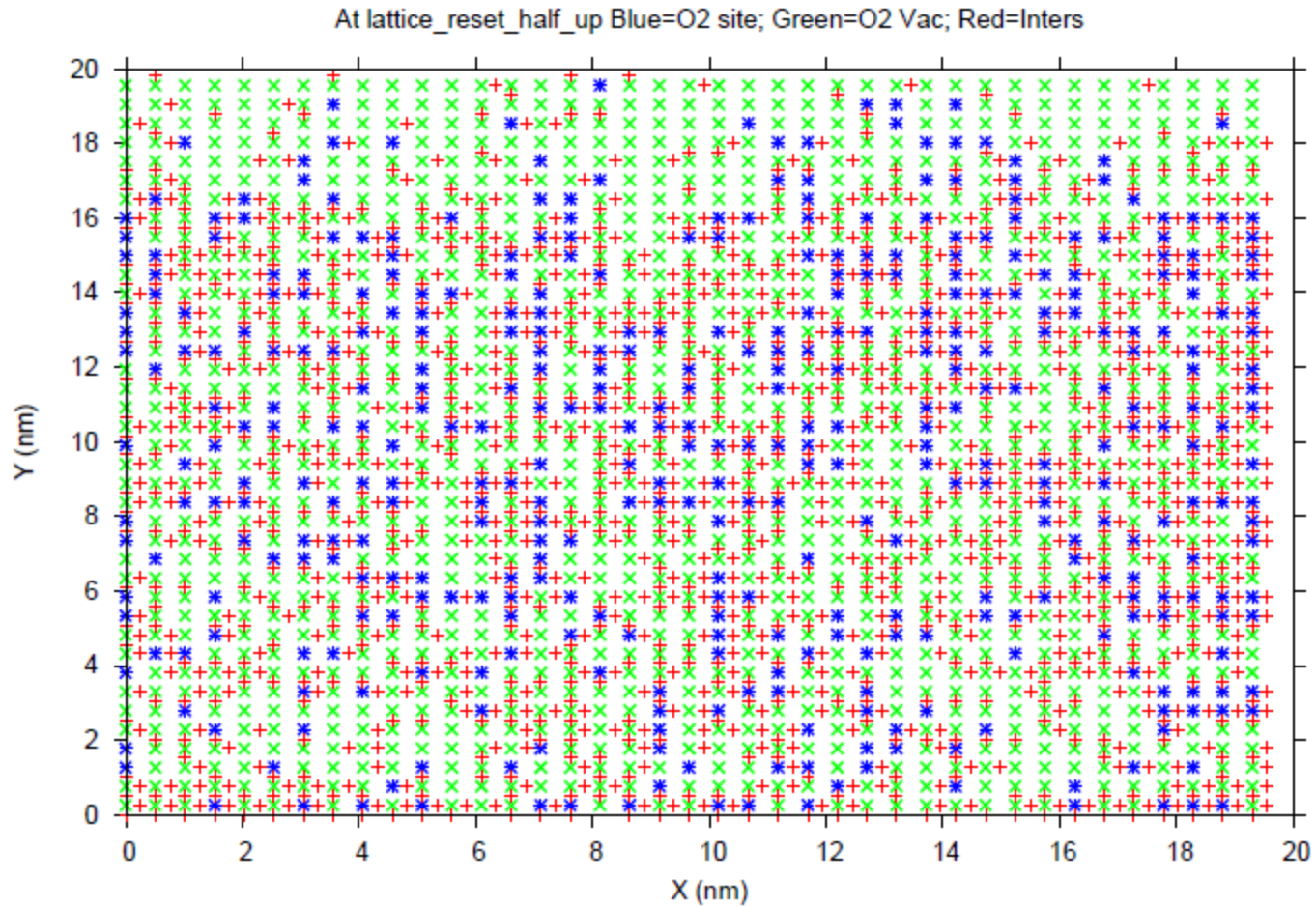
D:



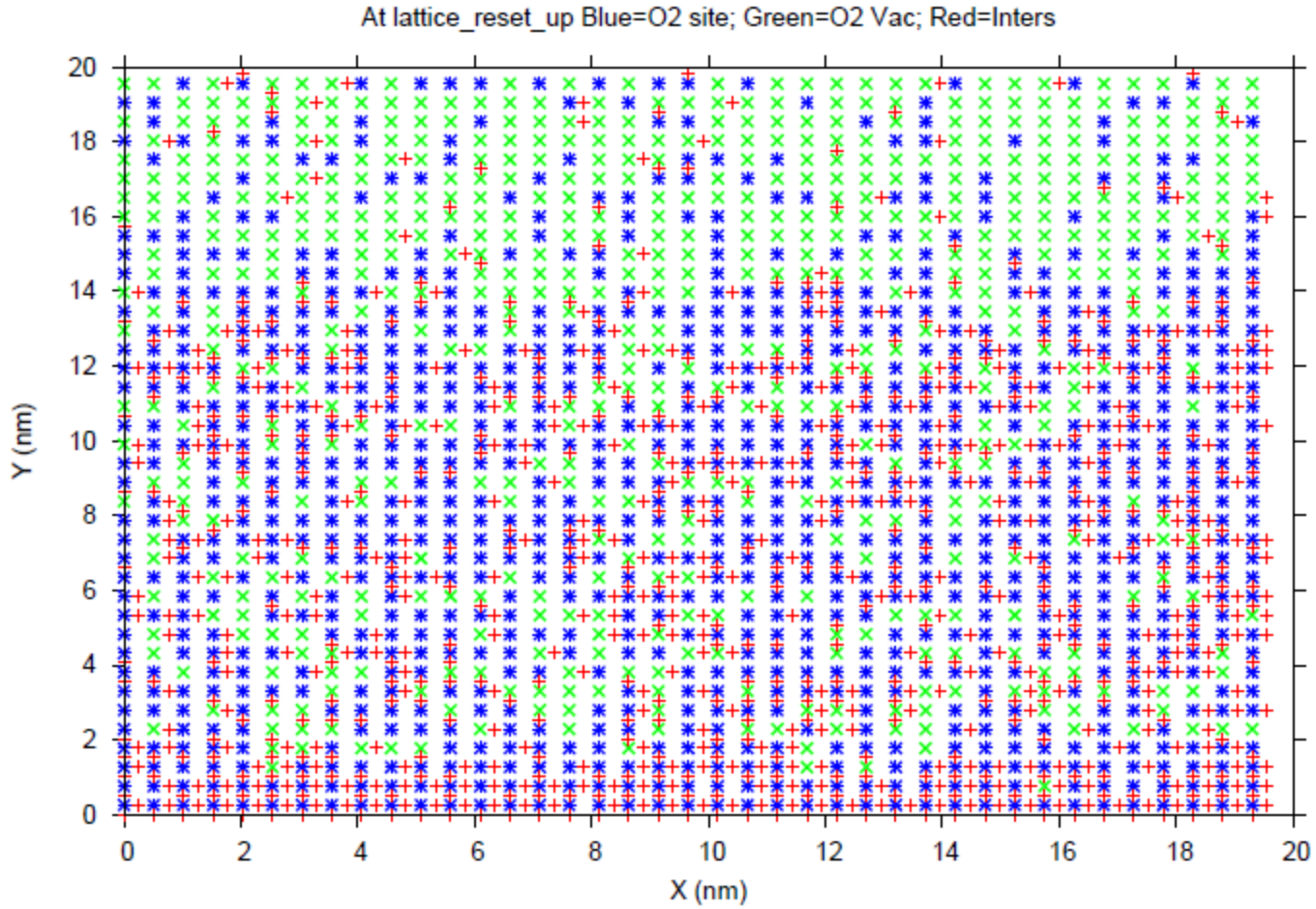
E:



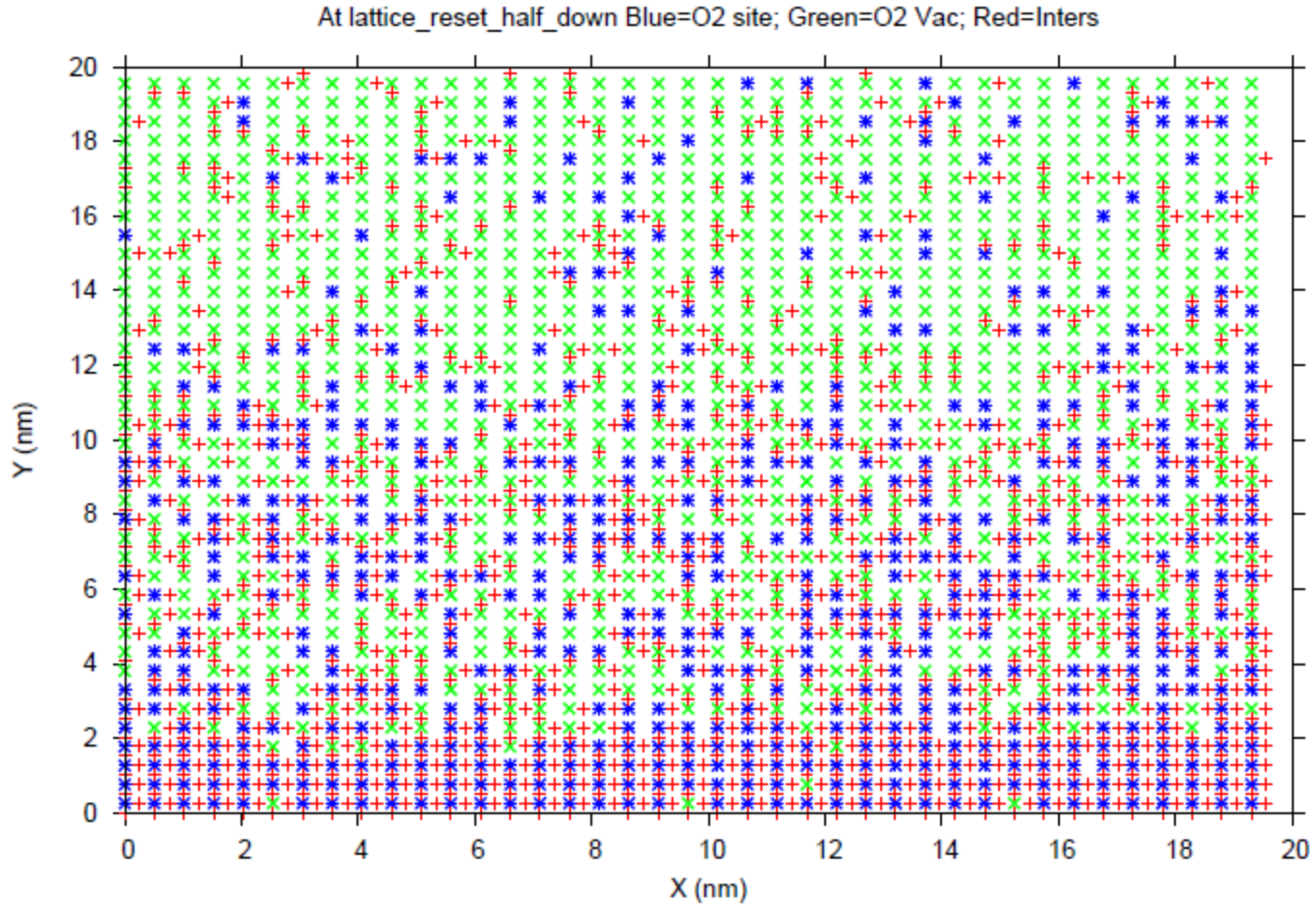
F:



G:

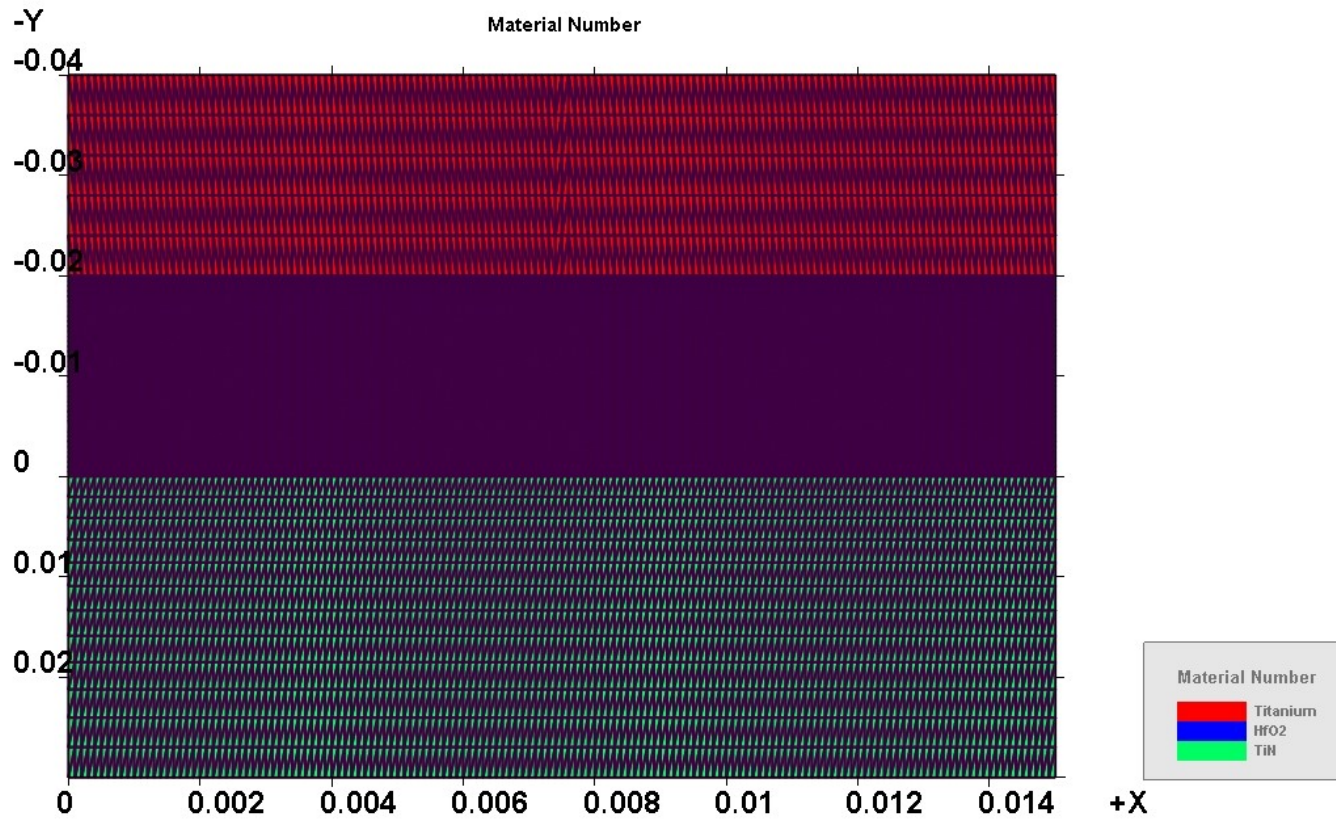


H:

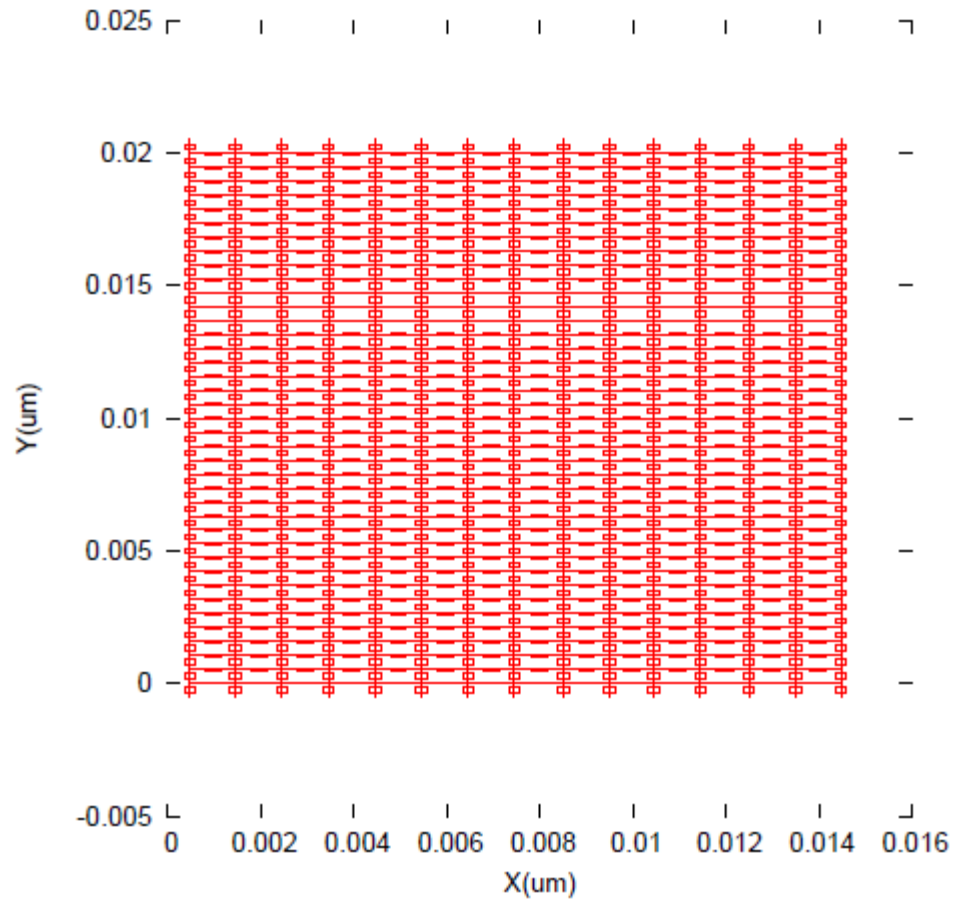


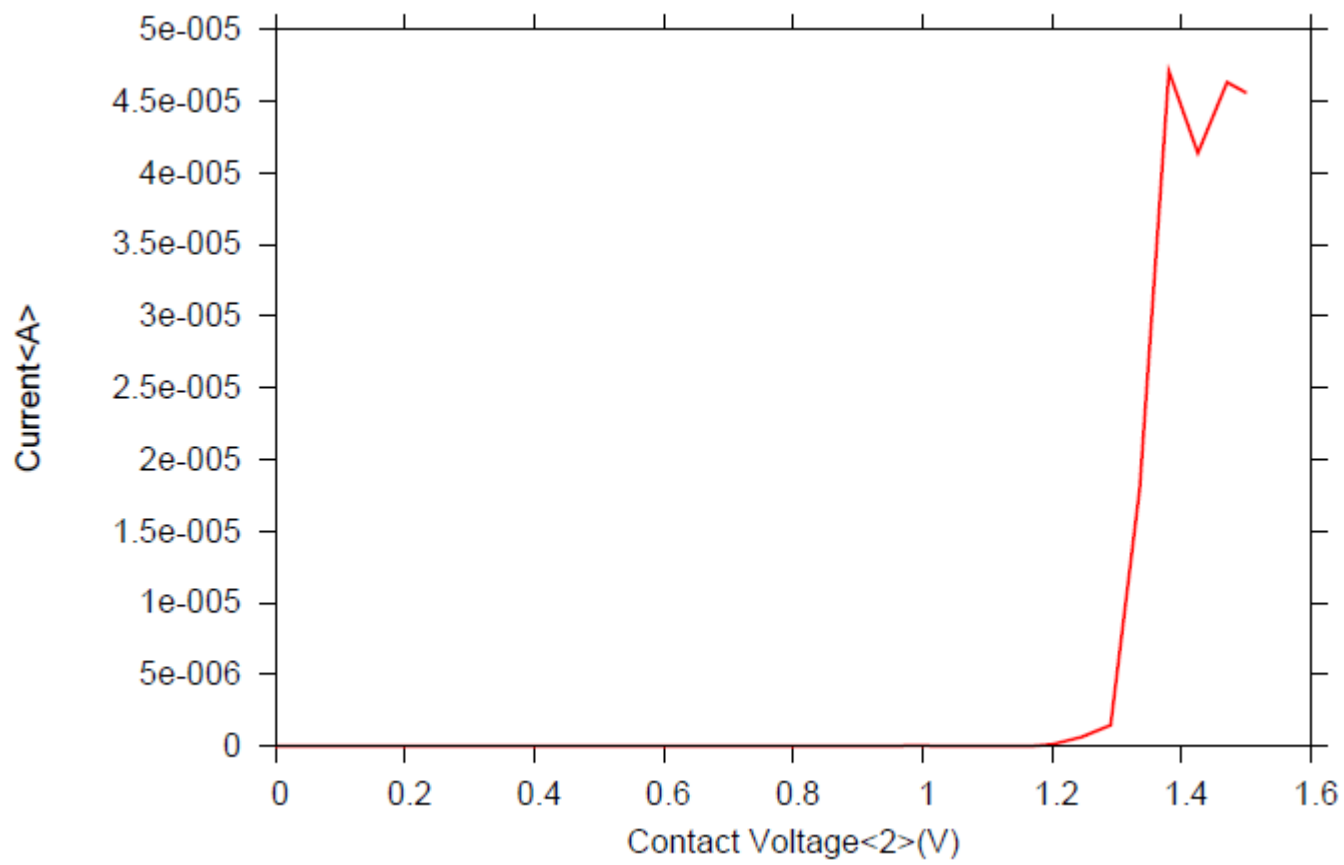


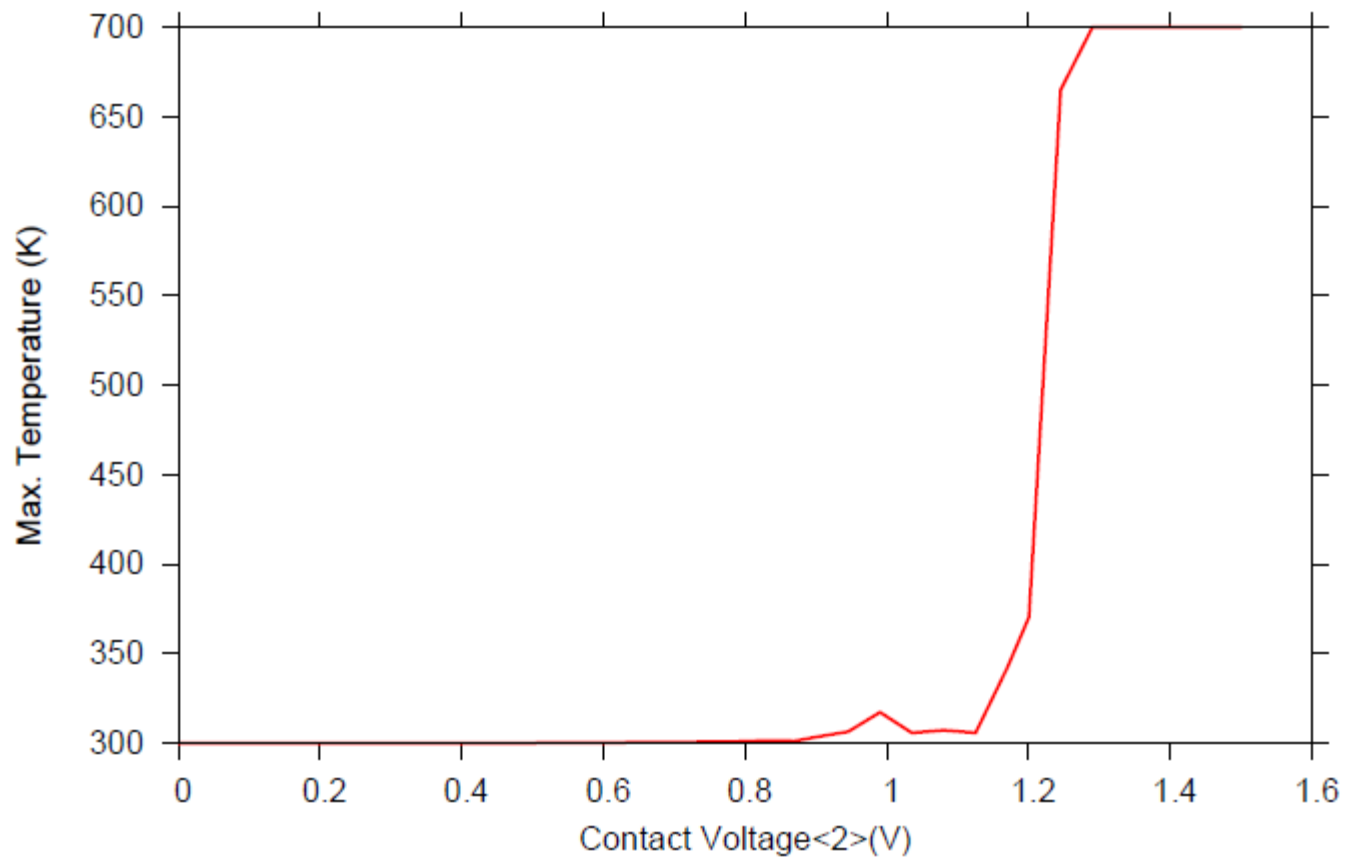
## Use of CSUPREM for TCAD mesh



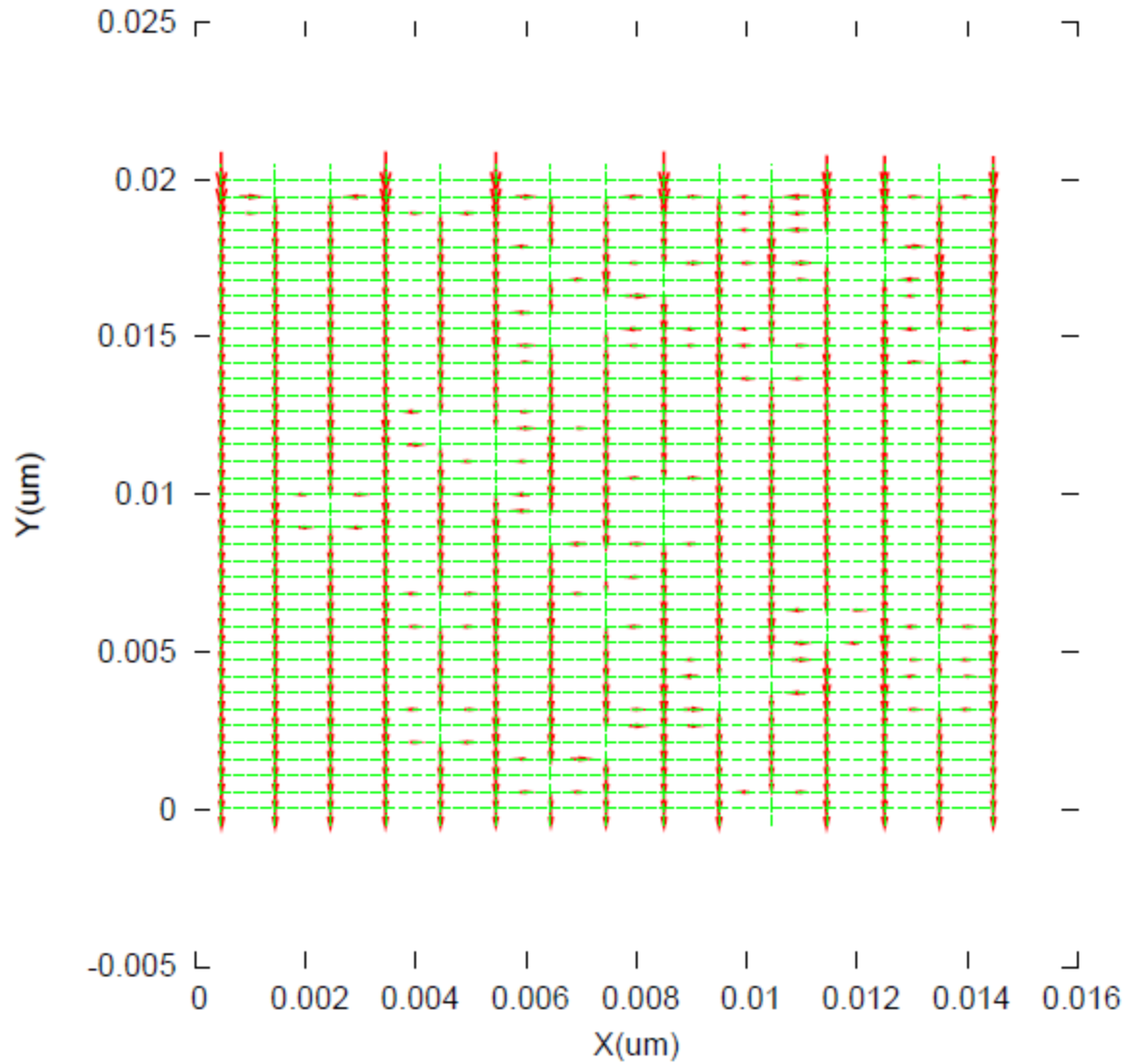
### Minispice circuit matrix





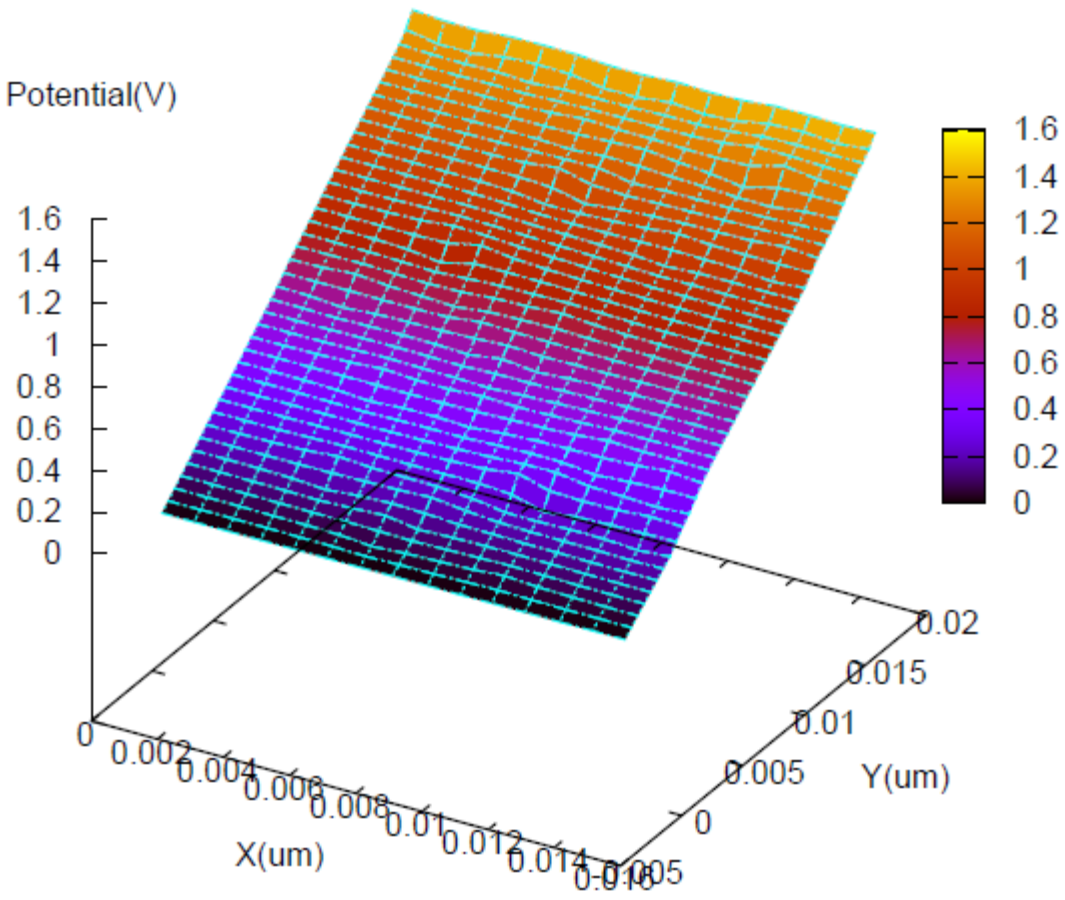


Max. Vector (A)=0.7221E-05

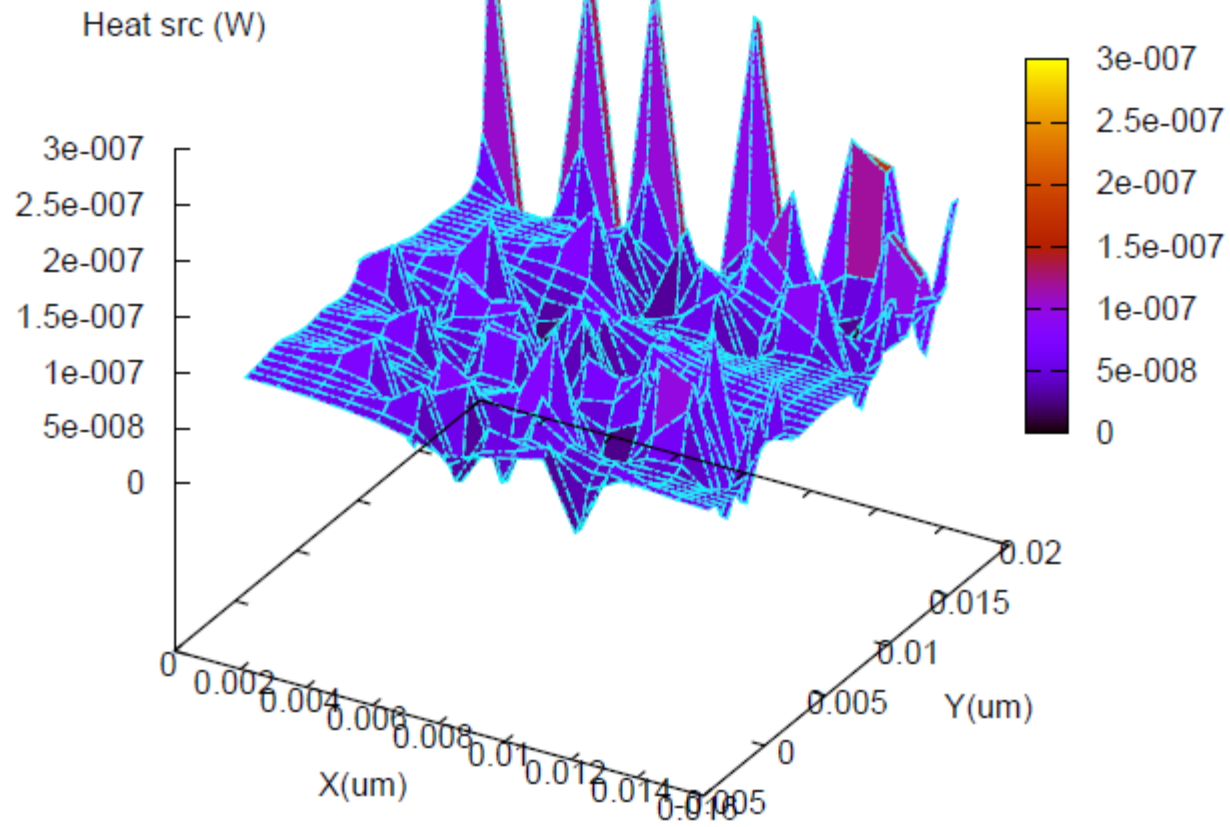


Potential (V)

Potential(V)



### Heat source



# Summary

- Monte Carlo method integrated with NovaTCAD mixmode.
- Basic set and reset characteristics demonstrated.
- Suitable for TCAD design as well as for research.